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Stocking Distributor

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[Diodes Incorporated](#)
[AP7217D-12YG-13](#)

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sales@integrated-circuit.com



AP7217D

1.2V 600mA CMOS LDO

Features

- Low Current Consumption: Typ. 40µA
- Output Voltage: 1.2V
- Guaranteed 600mA Output Current
- Dropout Voltage 850mV at 600mA Output Current
- Input Voltage Range: 2.5V to 5.5V
- Current Limit Protection
- Thermal shutdown Protection
- Stability with Low ESR Capacitors
- Low Temperature Coefficient
- SOT89-3L: Available in "Green" Molding Compound (No Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

General Description

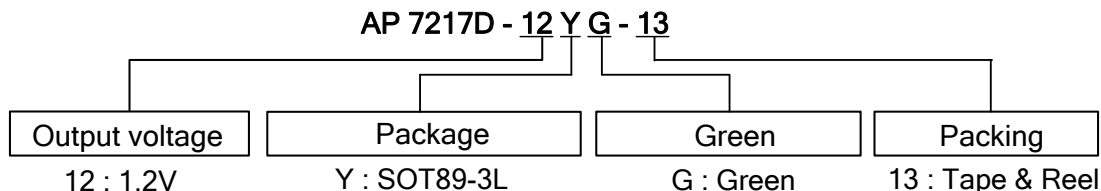
The AP7217D low-dropout linear regulator operates from 2.5V to 5.5V supply and delivers a guaranteed 600mA continuous load current.

The space-saving SOT89-3L package is suitable for "pocket" and hand-held application.

Applications

- CD and MP3 Players
- Cellular and PCS Phones
- Digital Still Camera
- Hand-Held Computers

Ordering Information



Device	Package Code	Packaging (Note 2)	13" Tape and Reel	
			Quantity	Part Number Suffix
AP7217D-12YG-13	Y	SOT89-3L	2500/Tape & Reel	-13

- Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead_free.html.
 2. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.



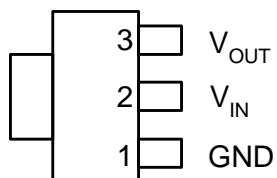
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Pin Assignments

(1) SOT89-3L

(Top View)

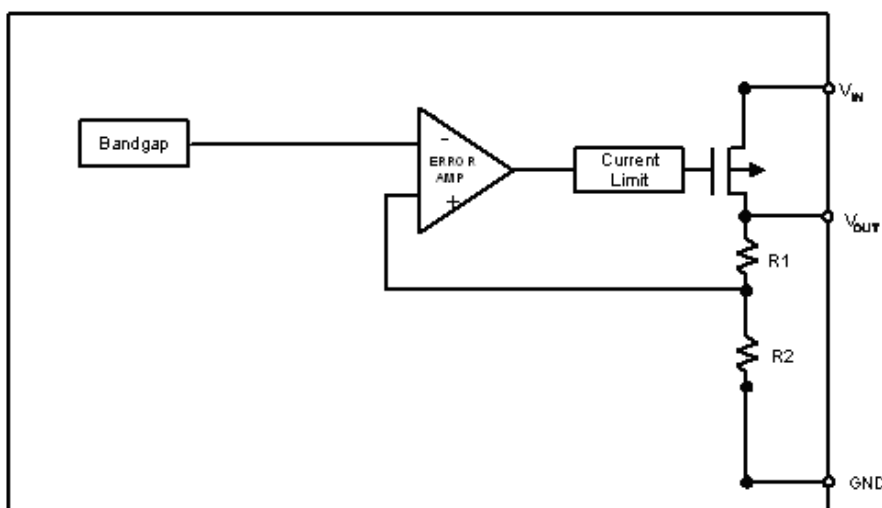


Tab is V_{IN}

Pin Descriptions

Pin Name	Pin No.	Function
GND	1	Ground
V_{IN}	2	Supply Voltage
V_{OUT}	3	Voltage Output

Block Diagram





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Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
ESD HBM	Human Body Model ESD Protection		3	KV
ESD MM	Machine Model ESD Protection		450	V
V _{IN}	Input Voltage		+6	V
P _D	Power Dissipation @ TA=25 °C (Note 3)	SOT89-3L	578	mW
T _{MJ}	Maximum Junction Temperature		150	°C

Notes: 3. Maximum P_D is under minimum recommended pad layout condition.

Recommended Operating Conditions

Symbol	Parameter	Min	Max	Unit
V _{IN}	Input Voltage	2.5	5.5	V
I _{OUT}	Output Current	0	600	mA
T _A	Operating Ambient Temperature	-40	85	°C
T _J	Operating Junction Temperature	-40	125	°C



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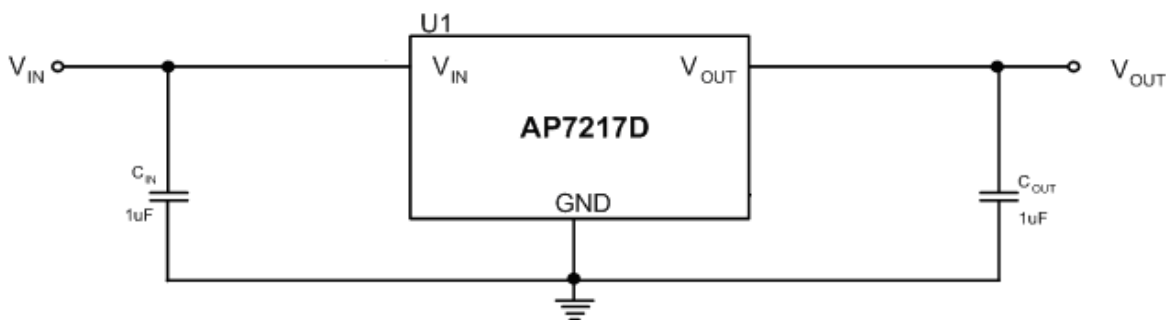
Electrical Characteristics

($T_A = 25^\circ\text{C}$, $C_{IN} = 1\mu\text{F}$, $C_{OUT} = 1\mu\text{F}$, $V_{IN} = 5\text{V}$, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
I_Q	Quiescent Current	$I_O = 0\text{mA}$	-	40	60	μA
V_{OUT}	Output Voltage Accuracy	$I_O = 30\text{mA}$	1.176	1.2	1.224	V
	V_{OUT} Temperature Coefficient	-40°C to 85°C , $I_{OUT} = 30\text{mA}$	-	± 100	-	ppm / $^\circ\text{C}$
$V_{DROPOUT}$	Dropout Voltage	$I_{OUT} = 600\text{mA}$, $V_{OUT} = 1.2\text{V}$	-	850	1300	mV
I_{OUT}	Maximum Output Current		600	-	-	mA
I_{LIMIT}	Current Limit		-	850	-	mA
I_{SHORT}	Short Circuit Current		-	200	-	mA
ΔV_{LINE}	Line Regulation	$2.5\text{V} \leq V_{IN} \leq 5.5\text{V}$; $I_{OUT} = 30\text{mA}$	-	0.2	-	%/V
ΔV_{LOAD}	Load Regulation (Note 4)	$1\text{mA} \leq I_{OUT} \leq 300\text{mA}$		15	35	mV
		$1\text{mA} \leq I_{OUT} \leq 600\text{mA}$		30	55	mV
PSRR	Power Supply Rejection	$V_{IN} = 4.3\text{V} + 0.5\text{Vp-pAC}$, $I_{OUT} = 50\text{mA}$, $F = 1\text{KHz}$	-	55	-	dB
	Thermal Shutdown Temperature		-	150	-	$^\circ\text{C}$
	Thermal Shutdown Hysteresis		-	30	-	$^\circ\text{C}$
θ_{JA}	Thermal Resistance Junction-to-Ambient	SOT89-3L (Note 5)	-	173	-	$^\circ\text{C/W}$
θ_{JC}	Thermal Resistance Junction-to-Case	SOT89-3L (Note 5)	-	51	-	$^\circ\text{C/W}$

Notes: 4. Regulation is measured at constant junction temperature by low duty cycle pulse testing.
 5. Test condition for SOT89-3L: Devices mounted on FR-4 substrate, single sided PC board, 2oz copper, with minimum recommended pad layout, no air flow.

Typical Application

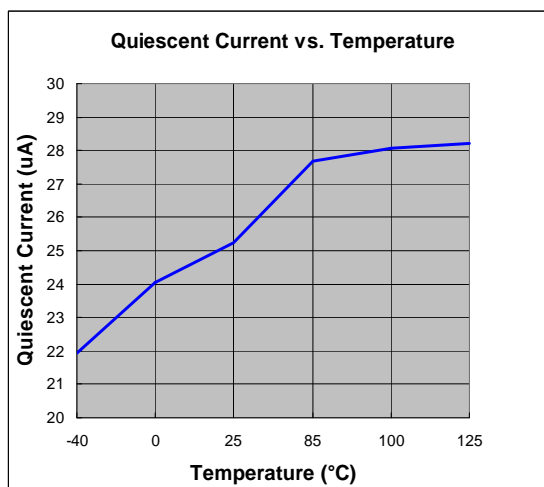
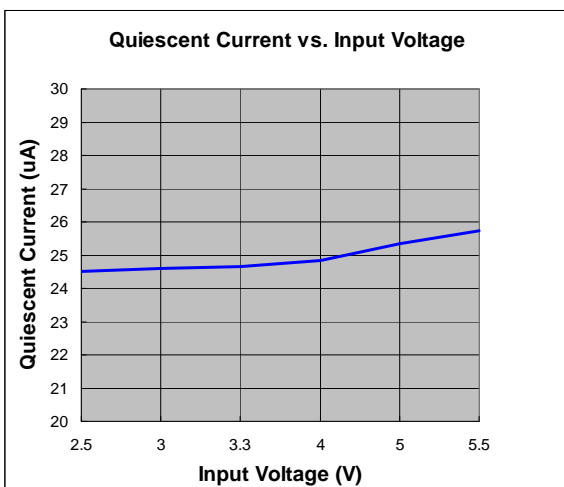
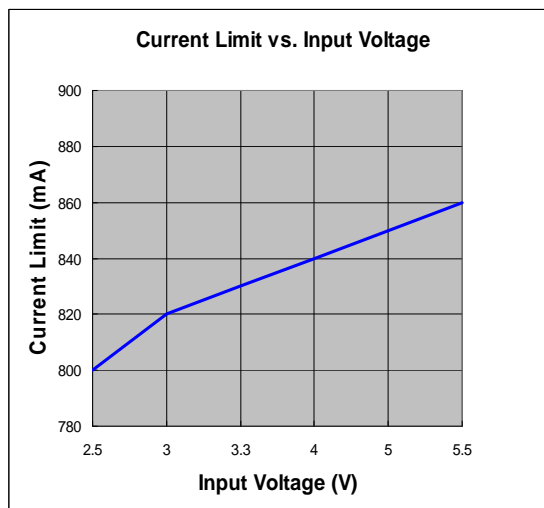
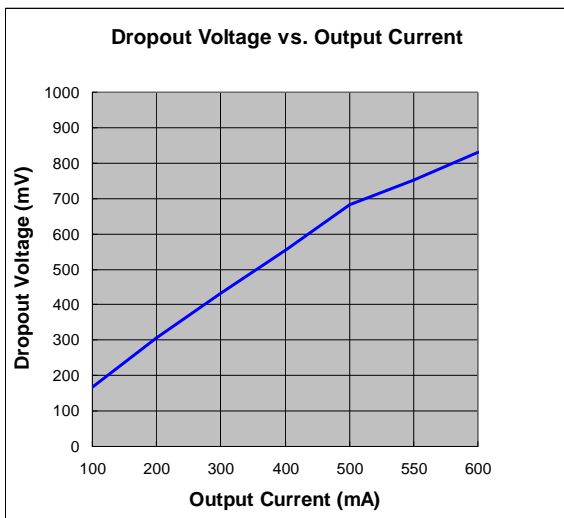




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Typical Performance Characteristics

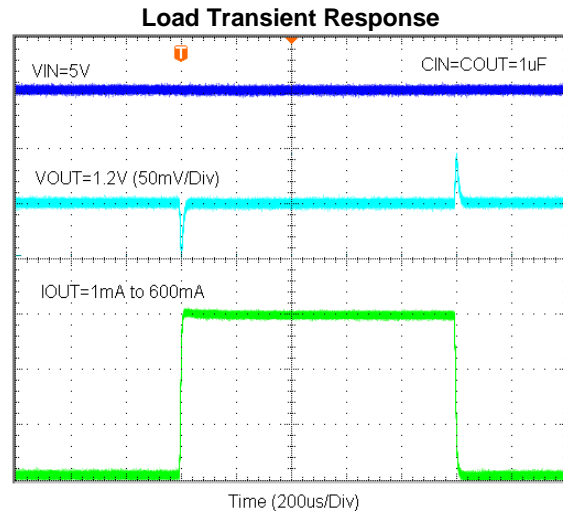
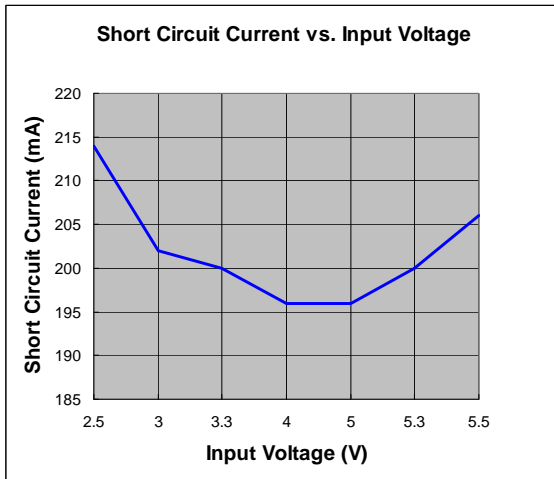




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Typical Performance Characteristics (Continued)





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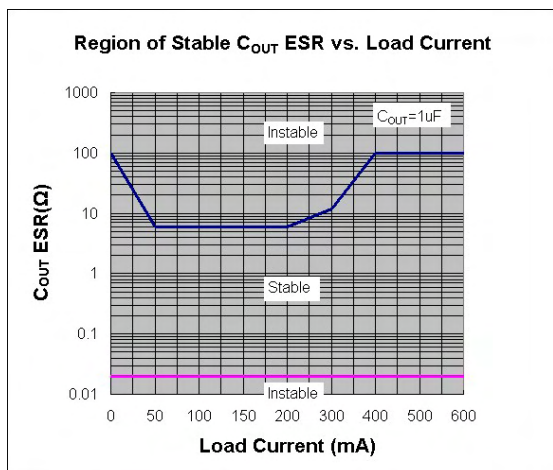
Application Information

Input Capacitor

A 1μF ceramic capacitor is recommended to connect between IN and GND pins to decouple input power supply glitch and noise. The amount of the capacitance may be increased without limit. A lower ESR (Equivalent Series Resistance) capacitor allows the use of less capacitance, while higher ESR type requires more capacitance. This input capacitor must be located as close as possible to the device to assure input stability and less noise. For PCB layout, a wide copper trace is required for both IN and GND.

Output Capacitor

The output capacitor is required to stabilize and help the transient response of the LDO. The AP7217D is designed to have excellent transient response for most applications with a small amount of output capacitance. The AP7217D is stable with any small ceramic output capacitors of 1.0μF or higher value, and the temperature coefficients of X7R or X5R type. Additional capacitance helps to reduce undershoot and overshoot during transient. For PCB layout, the output capacitor must be placed as close as possible to OUT and GND pins, and keep the leads as short as possible.



Thermal Considerations

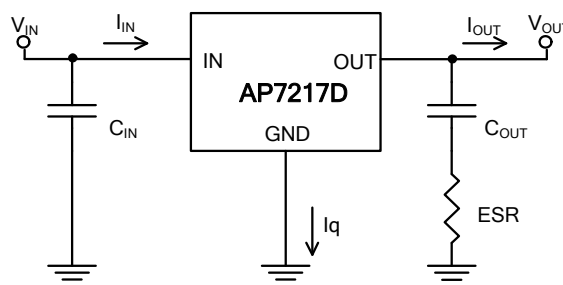
Thermal Shutdown Protection limits power dissipation in AP7217D. When the operation junction temperature exceeds 150°C, the Over Temperature Protection circuit starts the thermal shutdown function and turns the pass element off. The pass element turn on again after the junction temperature cools by 30°C. For continuous operation, do not exceed recommend maximum operation junction temperature 125°C. The power dissipation definition in device is:

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} + V_{IN} \times I_Q$$

The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surroundings airflow and temperature difference between junctions to ambient. The maximum power dissipation can be calculated by following formula:

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

Where $T_{J(MAX)}$ is the maximum operation junction temperature 125°C, T_A is the ambient temperature and the θ_{JA} is the junction to ambient thermal resistance.



Current Limit Protection

When output current at OUT pin is higher than current limit threshold, the current limit protection will be triggered and clamp the output current to approximately 850mA to prevent over-current and to protect the regulator from damage due to overheating.

Short circuit protection

When V_{OUT} pin is shorted to GND or V_{OUT} voltage is less than 200mV, short circuit protection will be triggered and clamp the output current to approximately 200mA.



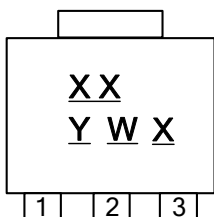
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Marking Information

(1) SOT89-3L

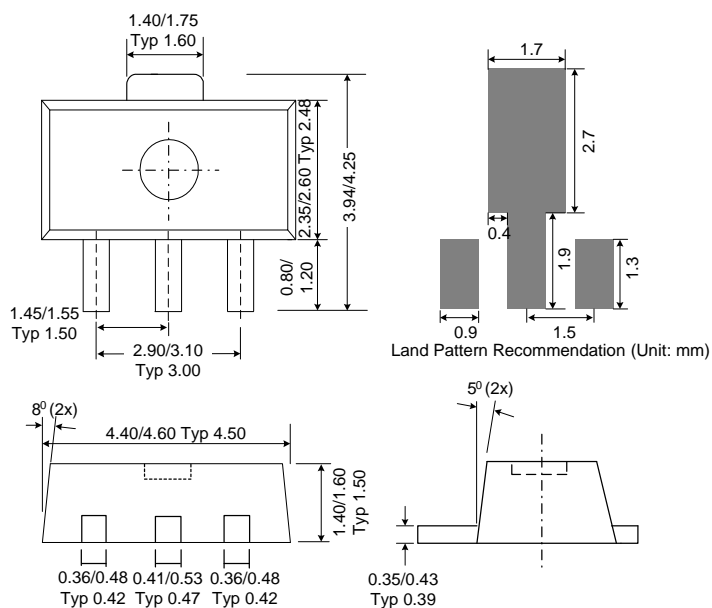
(Top View)



XX : N4 : AP7217D-12
Y : Year : 0~9
W : Week : A~Z : 1~26 week;
 a~z : 27~52 week;
 z represents 52 and 53 week
X : Internal code
 A~Z : Green

Package Information (All Dimensions in mm)

(1) Package Type: SOT89-3L





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